

SuperMOS – SOT-23 -20V BV_{DSS} , 90m Ω $R_{DS(on)}$, P-channel MOSFET

1. Description

The SI2301DS-ES is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product SI2301DS-ES is Pb-free.

2. Features

- -20V, $R_{DS(on)}=90m\Omega$ (TYP.) @ $V_{GS}=-4.5V$
 $R_{DS(on)}=110m\Omega$ (TYP.) @ $V_{GS}=-2.5V$
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
SI2301DS-ES	SOT-23	A1Ts	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7inches

Table-1 Ordering information

5. Pin Configuration and Functions

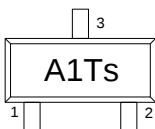
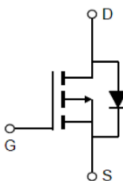
Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	-20	V
Gate-Source Voltage		V_{GS}	± 8	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	2.3	A
	$T_A=75^{\circ}\text{C}$		1.7	
Maximum Power Dissipation	$T_A=25^{\circ}\text{C}$	P_D	1.4	W
	$T_A=75^{\circ}\text{C}$		0.84	
Pulsed Drain Current		I_{DM}	9.2	A
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to +150	$^{\circ}\text{C}$

Thermal resistance ratings

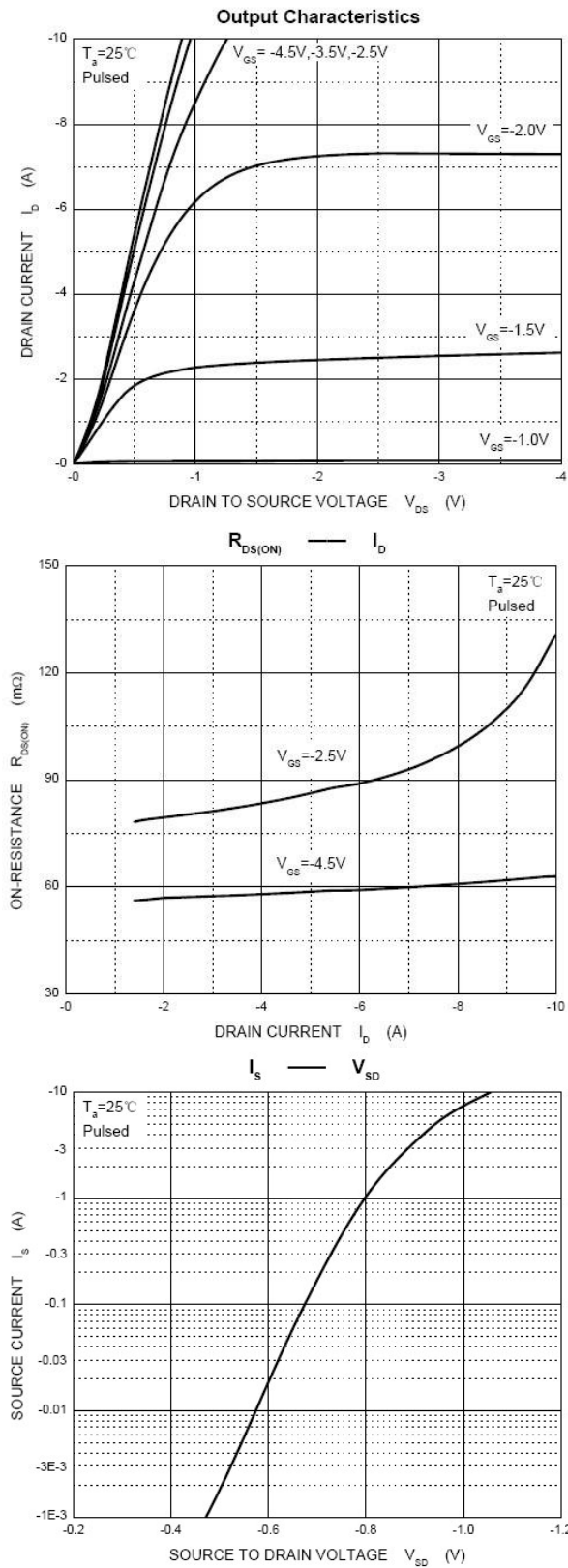
Single Operation			
Parameter	Symbol	Typical	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	90	$^{\circ}\text{C/W}$

Electrical Characteristics

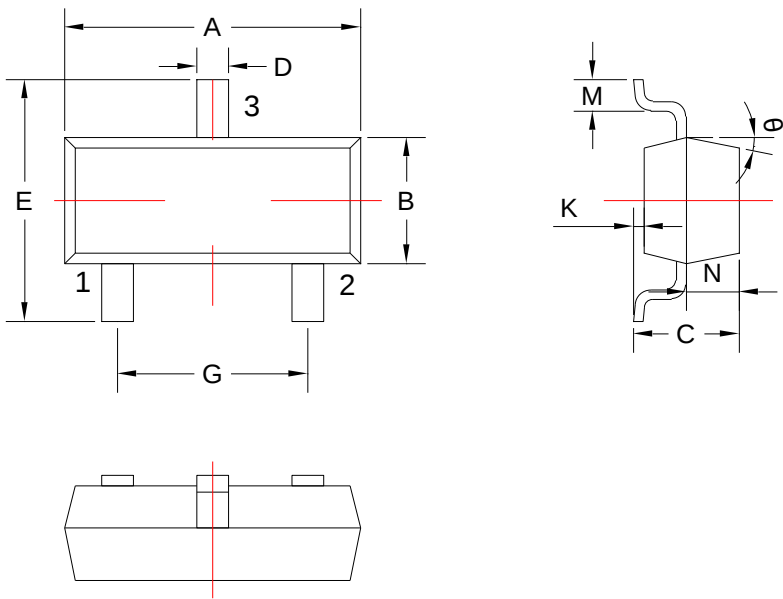
At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-0.4	-0.7	-1.0	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-2.3A		90	112	mΩ
		V _{GS} =-2.5V, I _D =-2A		110	142	
Forward trans conductance(a)	gfs	V _{DS} =-5V, I _D =-2.3A		6.5		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =-10V, f=1MHz			405	pF
Output Capacitance	C _{OSS}				75	
Reverse Transfer Capacitance	C _{RSS}				55	
Gate Resistance	R _g	f=1MHZ		6		Ω
Total Gate Charge	Q _{G(TOT)}	V _{GS} =-2.5V, V _{DS} =-10V, I _D =-2.3A		3.3	6	nC
Gate-to-Source Charge	Q _{GS}			0.7		
Gate-to-Drain Charge	Q _{GD}			1.3		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =-4.5V, V _{DS} =10V, R _L =10Ω, I _D =-1A, R _G =1Ω		11	20	ns
Rise Time	t _r			35	60	
Turn-Off Delay Time	t _{d(OFF)}			30	50	
Fall Time	t _f			10	20	
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-1.0A		-0.8	-1.5	V

7. Typical Characteristic



8. Dimension (SOT-23)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.85	3.04	G	1.80	2.00
B	1.20	1.40	K	0	0.10
C	0.90	1.10	M	0.20	-
D	0.40	0.50	N	0.50	0.70
E	2.25	2.55	θ	5°	9°

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